



Screened-Exchange Range-Separated Hybrid Functionals for heterogeneous systems

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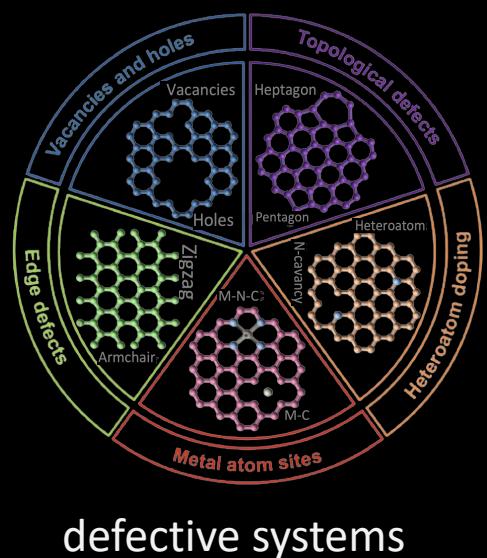
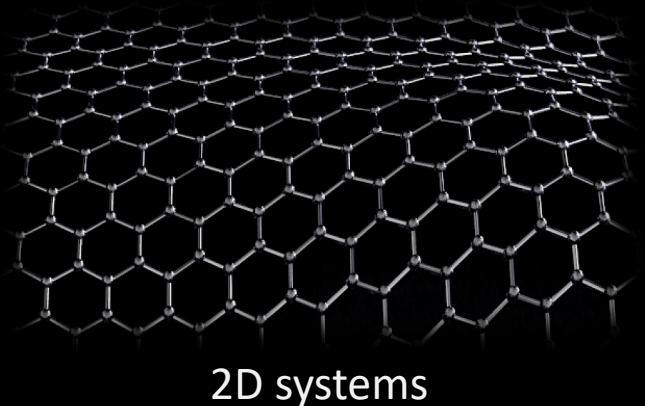
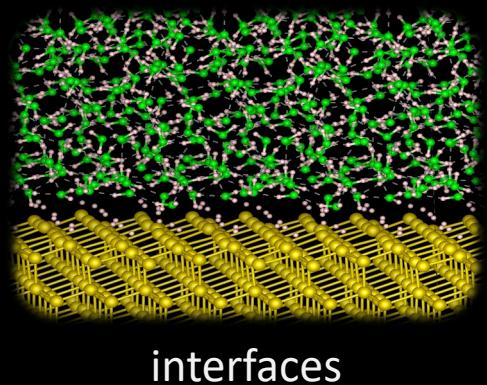
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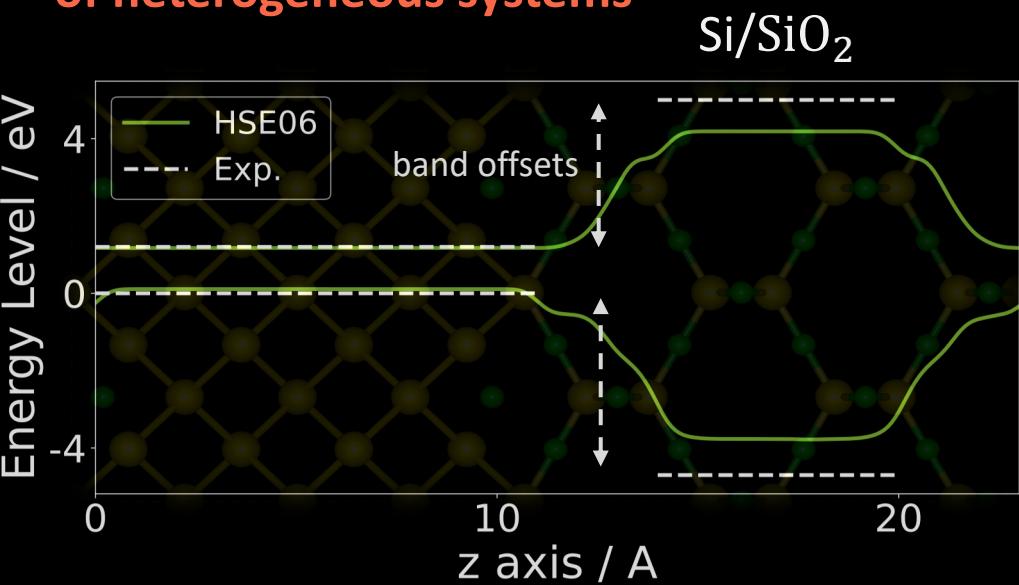
March 4, 2024

Introduction and Motivation

- **Materials** used in devices for the development of any technology exhibit inherent **heterogeneity**



- **Density Functional Theory (DFT)** has been widely and successfully used for decades to provide insight into the mechanisms that govern the behavior of materials
- However, it is still **challenging** for available exchange and correlation (xc) functionals to **describe with the same accuracy** the electronic properties of **different components of heterogeneous systems**



- Introduction to Screened-Exchange Range-Separated Hybrid (SE-RSH)
- Applications of SE-RSH to
 - analyze the electronic structures of heterogeneous systems:
 - Interfaces
 - Two-dimensional (2D) systems
 - Defective 2D systems
 - metal oxides
- Conclusions and future work

F. Gygi, Ibm J Res Dev **52**, 137 (2008)



Dielectric-Dependent Hybrid functional

Generalized Kohn-Sham theory:

$$\Sigma_x^{\text{GKS}} = \alpha \Sigma_x + (1 - \alpha) V_x^{\text{GGA}}$$

α → ratio of Fock exchange to semi-local



| Global Hybrid Functional^[1-2]:

α : constant number

| Range-Separated Hybrid Functional^[3-11]:

$$\begin{aligned} \Sigma_x^{\text{GKS}}(\mathbf{r}, \mathbf{r}') &= \alpha(\mathbf{r}, \mathbf{r}'; m, n, \mu) \odot \Sigma_x(\mathbf{r}, \mathbf{r}') \\ &+ (1 - m)V_x^{\text{GGA,lr}}(\mathbf{r}; \mu) \\ &+ (1 - n)V_x^{\text{GGA,sr}}(\mathbf{r}; \mu) \end{aligned}$$

- [1] P. Mori-Sánchez, A. J. Cohen, and W. Yang, *J Chem Phys* 125, 201102 (2006)
- [2] J. H. Skone, M. Govoni, and G. Galli, *Phys Rev B* 89, 195112 (2014)
- [3] J. Heyd, G. E. Scuseria, and M. Ernzerhof, *J Chem Phys* 124, 219906 (2006)
- [4] I. C. Gerber et al., *J Chem Phys* 127, 054101 (2007)
- [5] T. Yanai, D. P. Tew, and N. C. Handy, *Chem Phys Lett* 393, 51 (2004)
- [6] E. Weintraub, T. M. Henderson, and G. E. Scuseria, *J Chem Theory Comput* 5, 754 (2009)
- [7] W. Chen et al., *Phys Rev Mater* 2, 073803 (2018)
- [8] J. H. Skone, M. Govoni, and G. Galli, *Phys Rev B* 93, 235106 (2016)
- [9] D. K. Lewis, A. Ramasubramaniam, and S. Sharifzadeh, *Phys Rev Mater* 4, 063803 (2020)
- [10] G. Prokopiou et al., *J Chem Theory Comput* 18, 2331 (2022)
- [11] P. Borlido et al., *Npj Comput Mater* 6, 96 (2020)

Family of Dielectric-Dependent Hybrid:

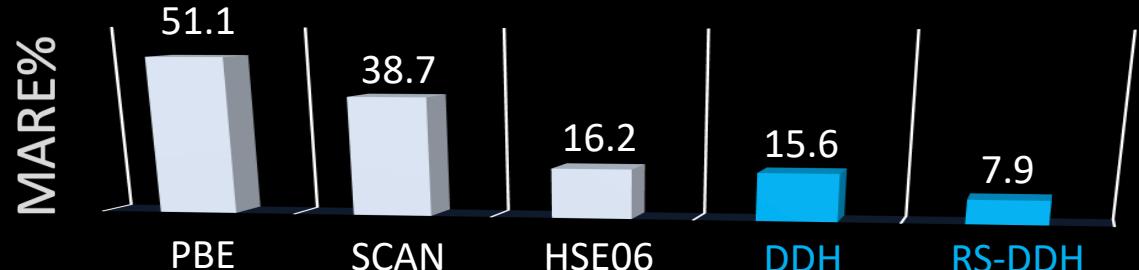
| Global Dielectric-Dependent Hybrid (DDH)^[1]

$$\alpha = \frac{1}{\epsilon_{\infty}^{\text{bulk}}}$$

| Range-Separated Dielectric-Dependent Hybrid (RS-DDH)^{[2][3]}

$$\alpha\left(\mathbf{r}, \mathbf{r}'; \frac{1}{\epsilon_{\infty}^{\text{bulk}}}, 1, \mu\right) = \frac{1}{\epsilon_{\infty}^{\text{bulk}}} + \left(1 - \frac{1}{\epsilon_{\infty}^{\text{bulk}}}\right) \text{erfc}(\mu|\mathbf{r} - \mathbf{r}'|)$$

Mean Average Relative Error [MARE%] for computed band gaps of semiconductors & insulators^[3]



Introduce spatial dependency into dielectric screening^[4-5]

Local dielectric function $\epsilon(\mathbf{r})$ via finite field method:

$$\Delta P(\mathbf{r}) = -e \sum_{i=1}^{N_w} \Delta \mathbf{r}_{wc}^i \delta(\mathbf{r} - \mathbf{r}_{wc}^i)$$
$$\epsilon_{\alpha\beta}(\mathbf{r}) = \delta_{\alpha\beta} + 4\pi \frac{\Delta P_\alpha(\mathbf{r})}{\Delta E_\beta(\mathbf{r})}$$

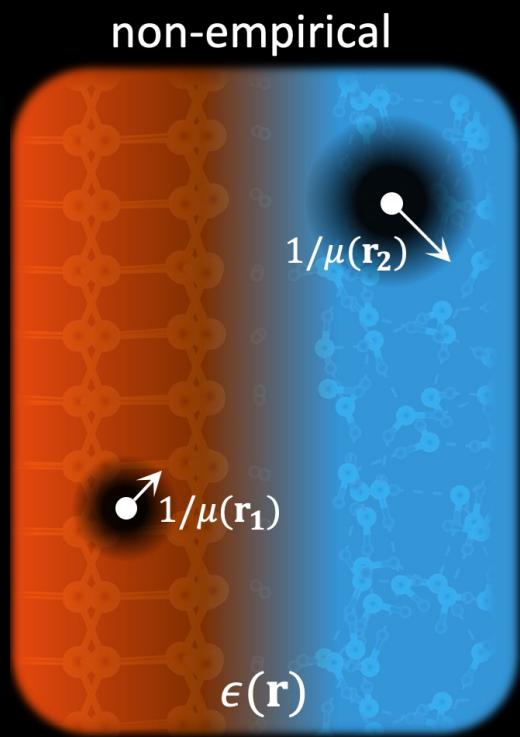
- [1] J. H. Skone, M. Govoni, and G. Galli, Phys Rev B 89, 195112 (2014)
- [2] W. Chen et al., Phys Rev Mater 2, 073803 (2018)
- [3] J. H. Skone, M. Govoni, and G. Galli, Phys Rev B 93, 235106 (2016)
- [4] H. Zheng, M. Govoni, and G. Galli, Phys Rev Mater 3, 073803 (2019)
- [5] P. Borlido, M. A. L. Marques, and S. Botti, J Chem Theory Comput 14, 939 (2018)

The **ratio** of Fock exchange to semi-local depends on position:

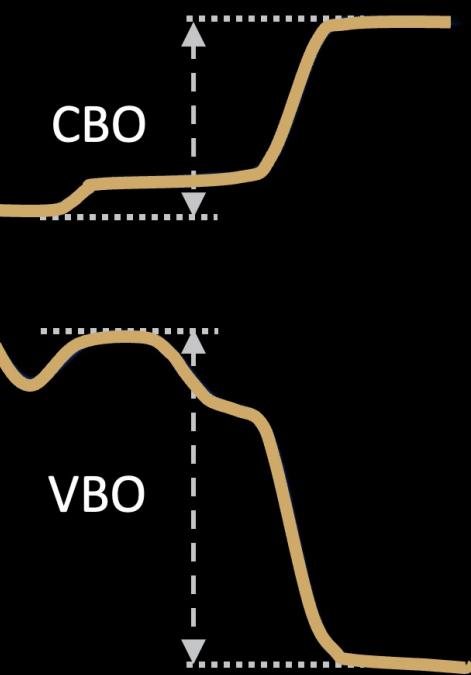
$$\alpha^{\text{SE-RSH}}(\mathbf{r}, \mathbf{r}'; \epsilon(\mathbf{r}), \mu(\mathbf{r})) = \frac{1}{\sqrt{\epsilon(\mathbf{r})\epsilon(\mathbf{r}')}} + \left(1 - \frac{1}{\sqrt{\epsilon(\mathbf{r})\epsilon(\mathbf{r}')}}\right) \text{erfc}(\mu(\mathbf{r})\mathbf{r}_{12})$$

long-range screening

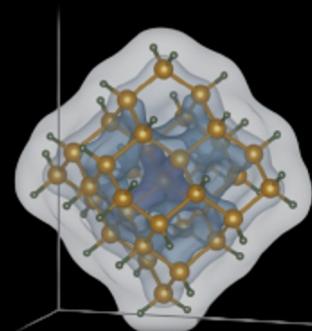
short-range screening



SE-RSH



Local dielectric function $\epsilon(\mathbf{r})$



Finite-field@PBE

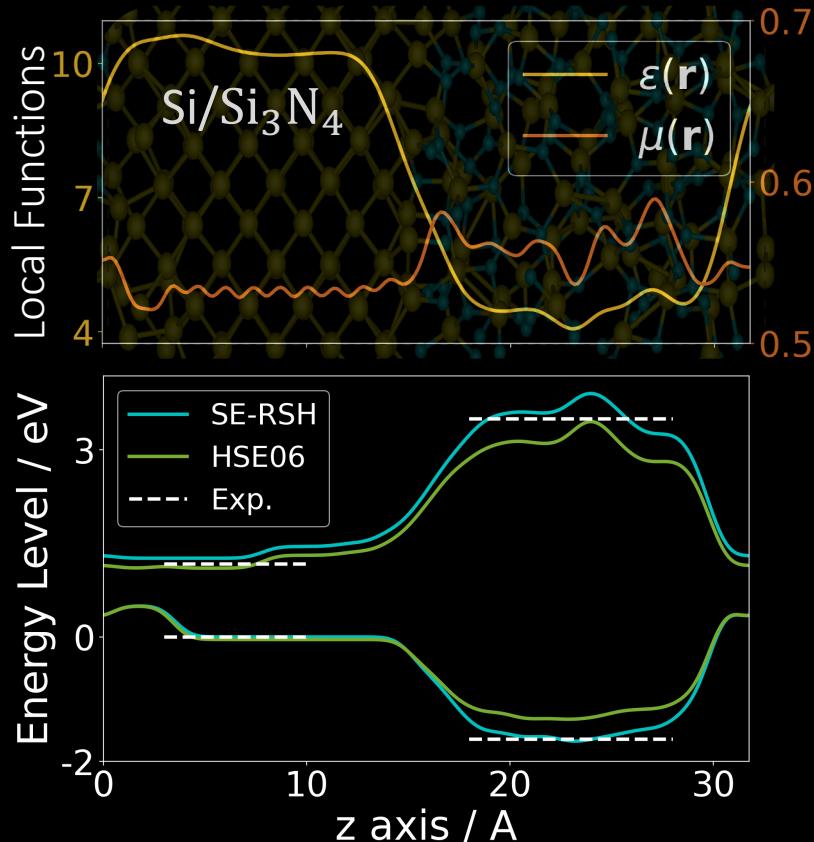
Local screening parameter $\mu(\mathbf{r})$

$$\mu(\mathbf{r}) = \frac{1}{2}k_{\text{TF}} = \left(\frac{3\rho(\mathbf{r})}{\pi}\right)^{1/6}$$

SE-RSH **generalizes** the definition of RS-DDH by introducing a **spatially dependent dielectric screening**.

Application of SE-RSH to heterogeneous systems

Band offset at interfaces

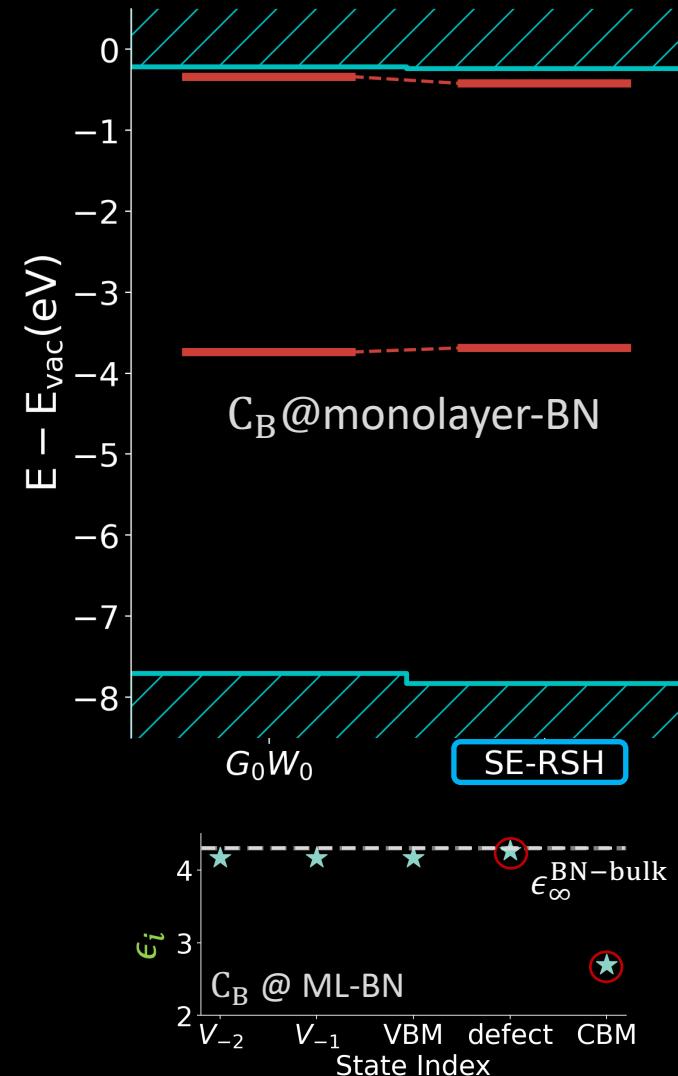


band gap (eV) of 2D systems

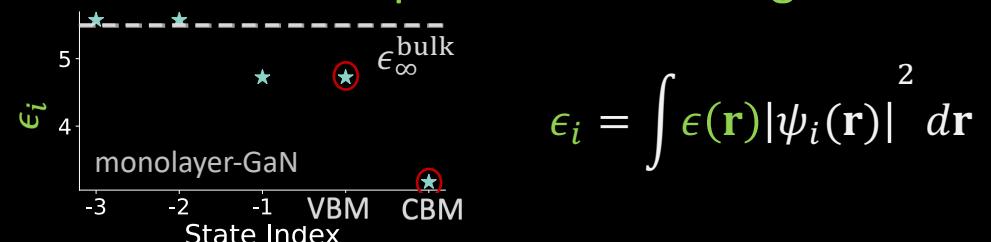
| systems* | HSE06 | SE-RSH | G_0W_0 [Ref.] |
|----------------|-------|--------|-----------------|
| phosphorene | 1.50 | 2.07 | 2.00 [2] |
| MoS_2 | 2.17 | 2.63 | 2.58 [3] |
| GaN | 3.53 | 4.41 | 4.44 [1] |
| ... | | | ... |
| BN | 5.7 | 7.59 | 7.49 [4] |
| MAE(eV) | 1.28 | 0.21 | |
| MARE(%) | 29.4 | 6.4 | |

* A total of 9 2D systems were tested

Defects in 2D systems

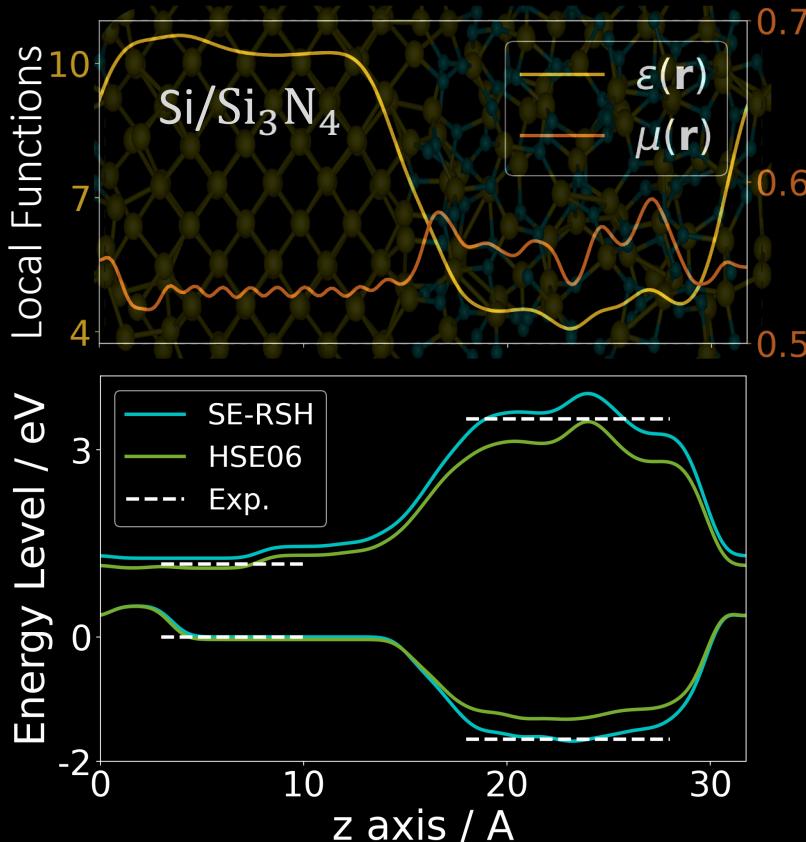


State-dependent screening



Application of SE-RSH to heterogeneous systems

Band offset at interfaces

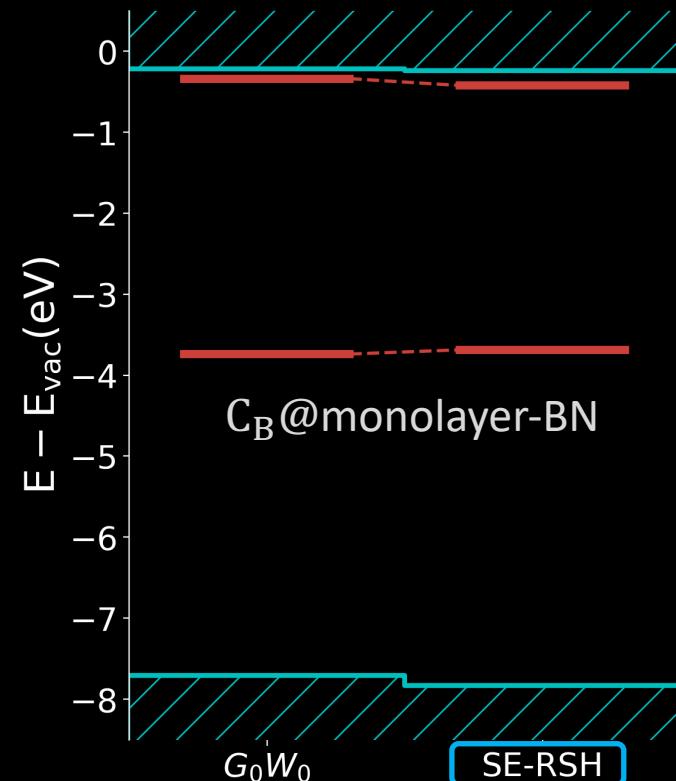


band gap (eV) of 2D systems

| systems* | HSE06 | SE-RSH | G_0W_0 [Ref.] |
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| phosphorene | 1.50 | 2.07 | 2.00 [2] |
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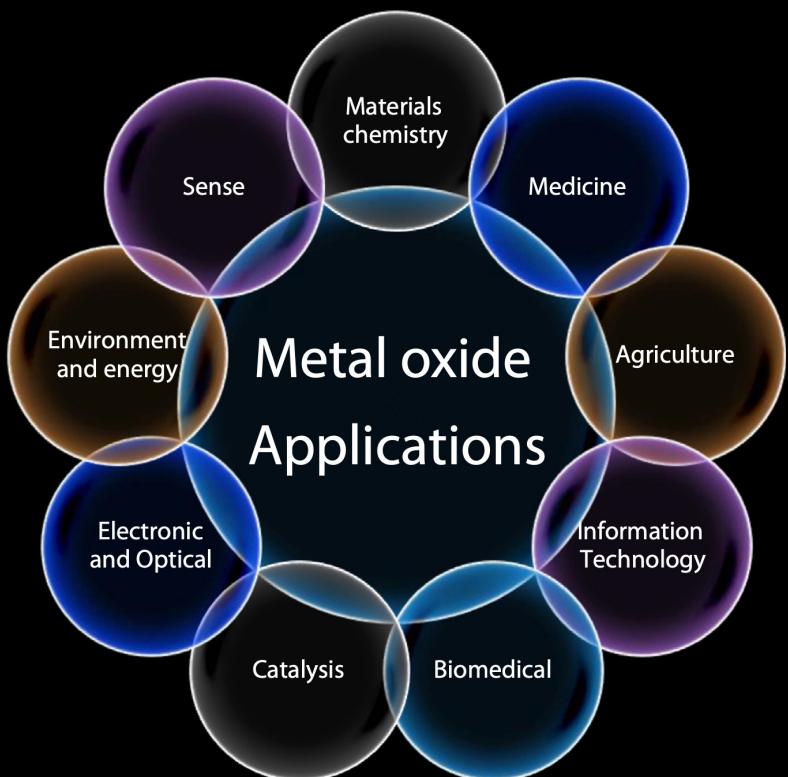
Defects in 2D systems



SE-RSH is a **nonempirical hybrid functional** that enable accurate calculations of the electronic properties of heterogeneous systems.

Controversial results for metal oxides

- Applications of metal oxides are found in a wide range of fields.



Dielectric-Dependent Hybrid functionals tends to **overestimate** the bandgap of metal oxide.

| systems | DD-RSH-CAM* [1] | Exp. + ZPR |
|--------------------------------|-----------------|-----------------|
| In ₂ O ₃ | 3.51 | 2.7 ~ 2.9 [2] |
| TiO ₂ | 4.18 | 3.65 ~ 3.95 [3] |
| MnO | 4.93 | 3.9~4.1 [4] |
| CoO | 5.61 | 2.6 [4] |
| NiO | 6.34 | 4.0 ~ 4.3 [4] |

*DD-RSH-CAM is a dielectric-dependent hybrid that achieve high accuracy in various semiconductors and insulators.

[1] Chen, Wei, et al. *Phys. Rev. Mater.* 2.7 (2018)

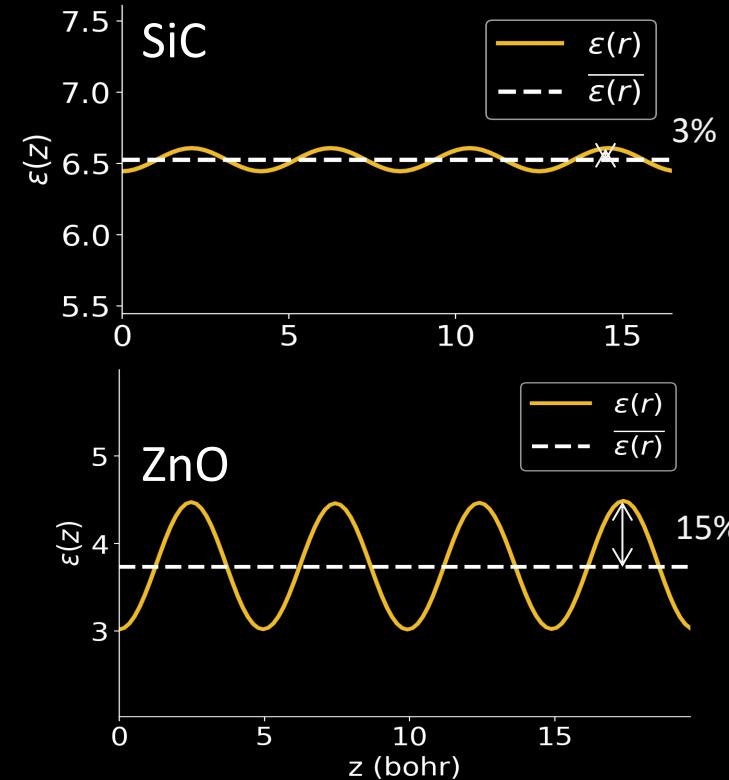
[2] Scherer, V., et al., *Appl. Phys. Lett.* 100.21 (2012)

[3] Rangan, Sylvie, et al. *J. Phys. Chem. C.* 114.2 (2010)

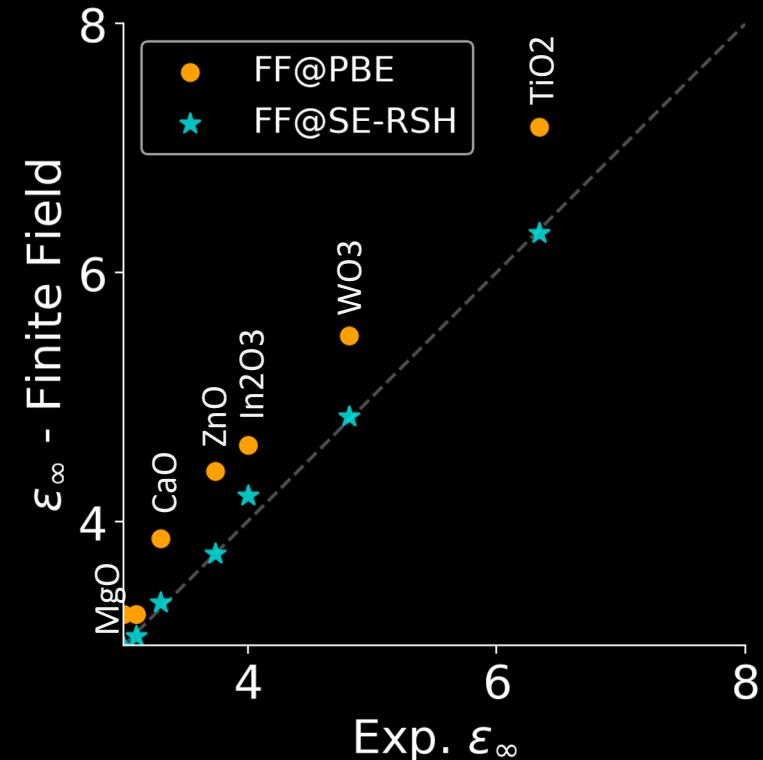
[4] P. Liu et al., *J. Phys.: Condens. Matter.* 32, 015502 (2019)

Spatial dependence of screening in metal oxides

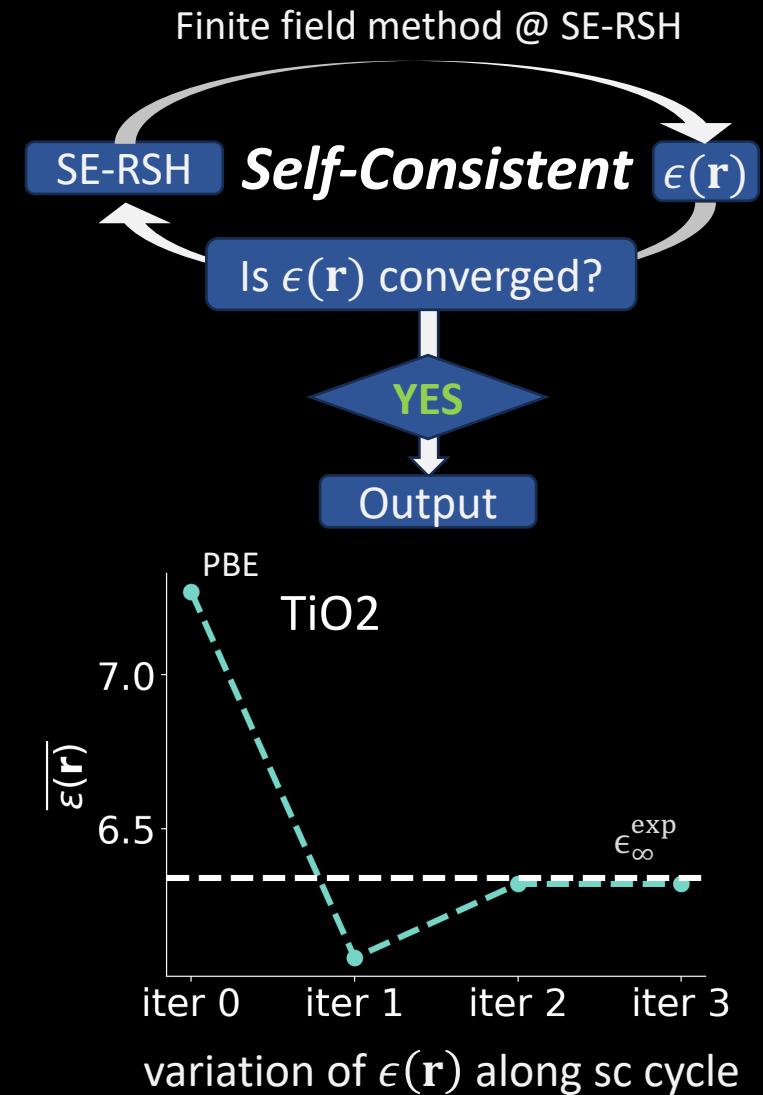
Challenges in applying DDH to metal oxides:



Marked spatial dependence of screening in ionic-bonded systems.



Calculation of ϵ @ PBE overestimates screening



Application of SE-RSH to metal oxides

Electronic band gap (eV) of metal oxides

| systems* | DD-RSH-CAM _[1] | SE-RSH | Exp. + ZPR |
|--------------------------------|---------------------------|--------|-----------------|
| In ₂ O ₃ | 3.51 | 2.99 | 2.7 ~ 2.9 [2] |
| TiO ₂ | 4.18 | 4.02 | 3.65 ~ 3.95 [3] |
| ZnO | 3.74 | 3.56 | 3.61 [4] |
| Al ₂ O ₃ | 9.51 | 9.45 | 9.1 ~ 9.5 [5] |
| CaO | 7.17 | 7.05 | 7.43 [6] |
| MgO | 8.19 | 8.17 | 8.3 [7] |
| WO ₃ | 3.92 | 3.70 | 3.7 ~ 3.8 [8] |
| MAE(eV) | 0.286 | 0.213 | |
| MARE(%) | 6.87 | 3.70 | |

[1] Chen, Wei, et al. *Phys. Rev. Mater.* 2.7 (2018)

[2] Scherer, V., et al., *Appl. Phys. Lett.* 100.21 (2012)

[3] Rangan, Sylvie, et al. *J. Phys. Chem. C.* 114.2 (2010)

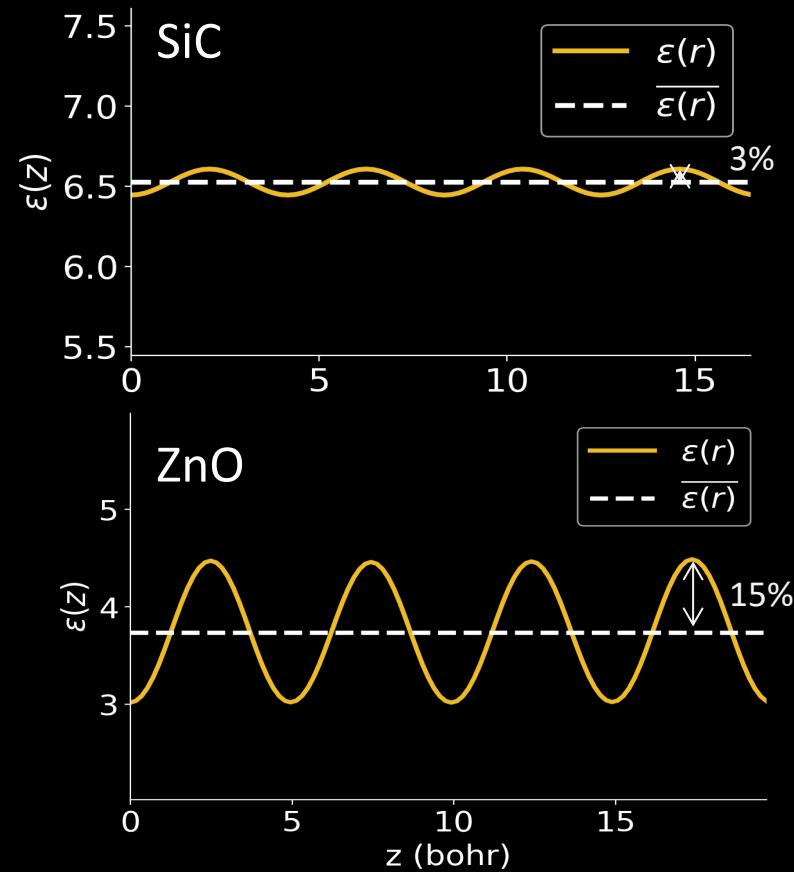
[4] Reynolds, D. C., et al. *Phys. Rev. B* 60.4 (1999)

[5] French, Roger H., *J. Am. Ceram. Soc.* 73.3 (1990)

[6] Whited, R. C. et al. *Solid State Commun.* 13.11 (1973)

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[8] Meyer, Jens, et al. *Appl. Phys. Lett.* 96.19 (2010)



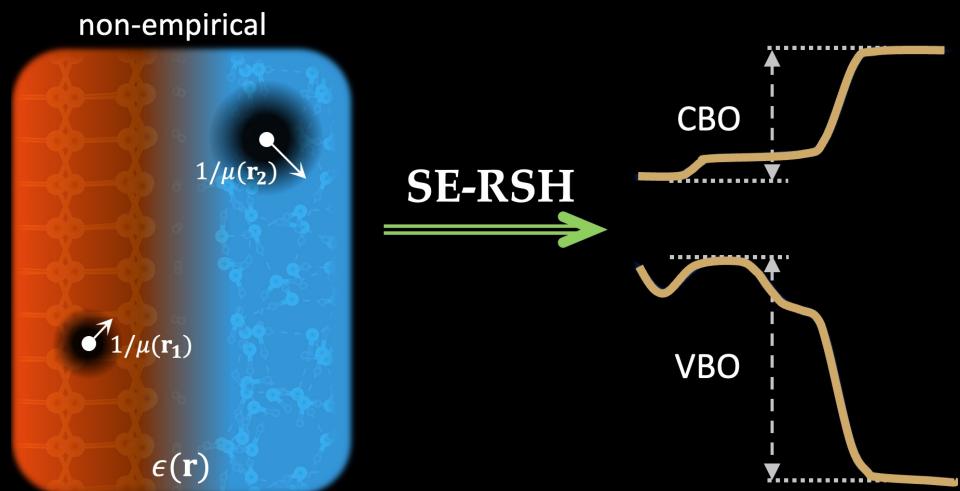
SE-RSH results appear to be more accurate than RSH results, due to the inclusion of the spatial variation of the screening.

Conclusions and future work

We proposed a nonempirical range-separated hybrid functional with spatially dependent screened exchange, SE-RSH, enabling accurate calculations of the electronic properties of heterogeneous systems and metal oxides.

The validation of our results for diverse materials shows that:

1. Utilization of local dielectric function $\epsilon(\mathbf{r})$ help SE-RSH achieve high accuracy.
2. Metal oxides exhibit a strong spatial variation of the screening, which is captured by SE-RSH.



Future Work

1. Study metal-oxide interfaces w/wo defects.
2. Integrate Time-Dependent Density Functional Theory (TDDFT) with SE-RSH.
3. Accelerate exact exchange calculations in SE-RSH for modeling large-scale complex systems.

Acknowledgement



The
GALLI
GROUP

@ The University of Chicago

$$i\hbar \frac{\partial \psi}{\partial t} = -\frac{\hbar^2}{2m} \nabla^2 \psi + V \psi$$



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$$\sum_j \langle ij | \alpha \odot v_c | ji \rangle \quad \text{vs.} \quad \sum_j \langle ij | \epsilon^{-1} v_c | ji \rangle$$

ϵ^{-1} : full dielectric matrix

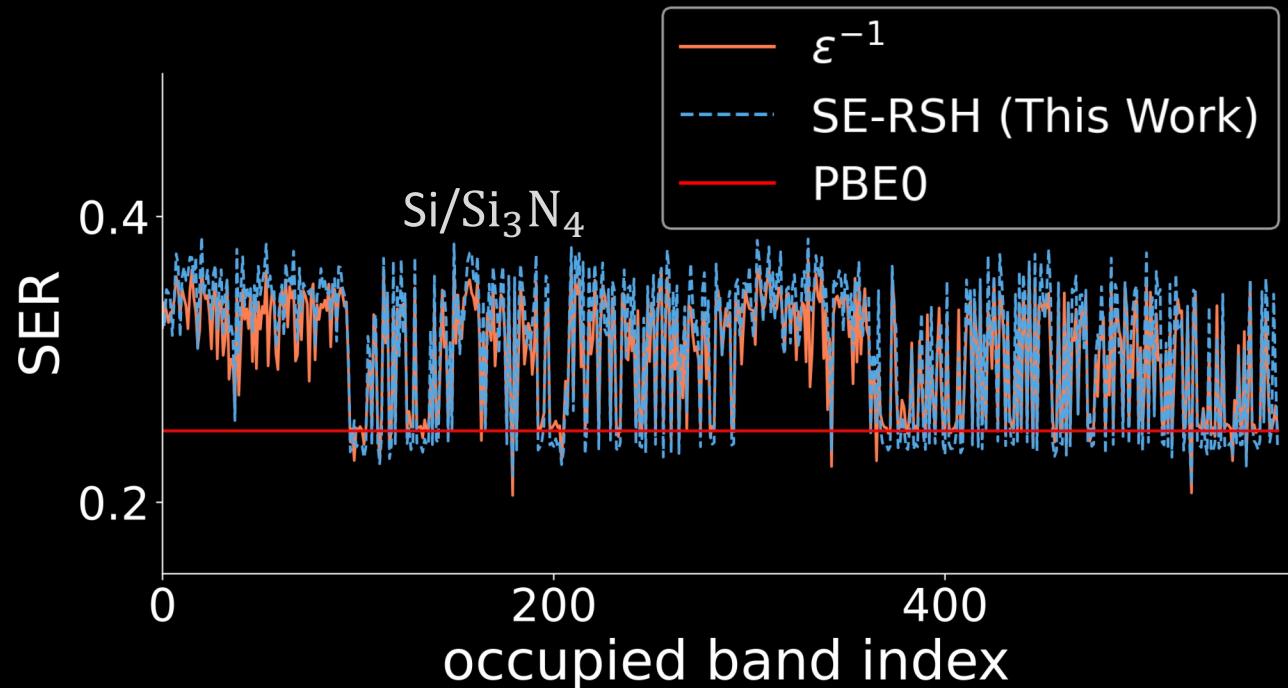
v_c : bared coulomb interaction

$\{|i\rangle\}$: Maximally Localized Wannier Functions

screened exchange ratio (SER):

$$SER_i^\alpha = \frac{\sum_j \langle ij | \alpha \odot v_c | ji \rangle}{\sum_j \langle ij | v_c | ji \rangle}$$

$$SER_i^{\epsilon^{-1}} = \frac{\sum_j \langle ij | \epsilon^{-1} v_c | ji \rangle}{\sum_j \langle ij | v_c | ji \rangle}$$



α^{SE-RSH} effectively approximates and accurately describes non-dynamical screening